

# SGF80N60UF

## Ultra-Fast IGBT

### General Description

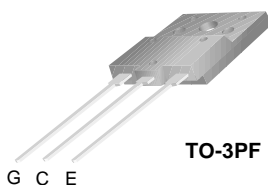
Fairchild's Insulated Gate Bipolar Transistor(IGBT) UF series provides low conduction and switching losses. UF series is designed for the applications such as motor control and general inverters where High Speed Switching is required.

### Features

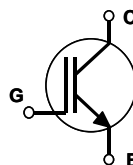
- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 2.1\text{ V @ } I_C = 40\text{ A}$
- High Input Impedance

### Application

AC & DC Motor controls, General Purpose Inverters, Robotics, Servo Controls



TO-3PF



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description	SGF80N60UF	Units
V <sub>CES</sub>	Collector-Emitter Voltage	600	V
V <sub>GES</sub>	Gate-Emitter Voltage	± 20	V
I <sub>C</sub>	Collector Current @ T <sub>C</sub> = 25°C	80	A
	Collector Current @ T <sub>C</sub> = 100°C	40	A
I <sub>CM(1)</sub>	Pulsed Collector Current	220	A
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C	110	W
	Maximum Power Dissipation @ T <sub>C</sub> = 100°C	45	W
T <sub>J</sub>	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	°C

**Notes :**

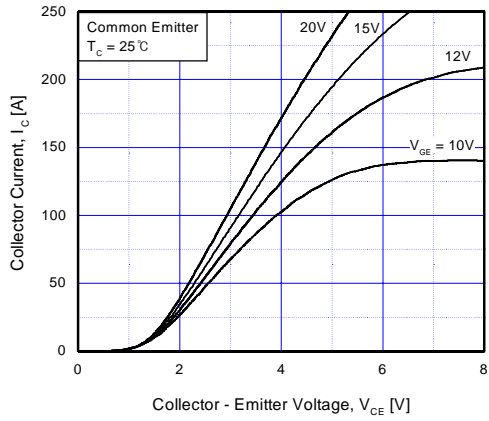
(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

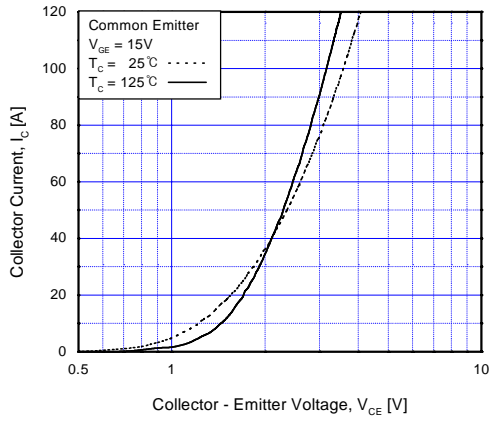
Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	1.1	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

**Electrical Characteristics of IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

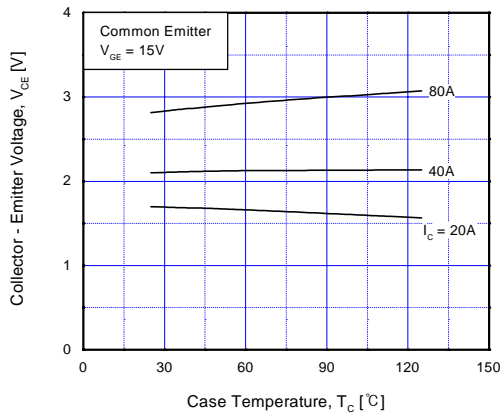
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 40mA, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	--	2.1	2.6	V
		$I_C = 80A, V_{GE} = 15V$	--	2.6	--	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	2790	--	pF
$C_{oes}$	Output Capacitance		--	350	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	100	--	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	23	--	ns
$t_r$	Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	130	ns
$t_f$	Fall Time		--	50	150	ns
$E_{on}$	Turn-On Switching Loss		--	570	--	$\mu J$
$E_{off}$	Turn-Off Switching Loss		--	590	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	1160	1500	$\mu J$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	30	--	ns
$t_r$	Rise Time		--	55	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	200	ns
$t_f$	Fall Time		--	160	250	ns
$E_{on}$	Turn- On Switching Loss		--	630	--	$\mu J$
$E_{off}$	Turn- Off Switching Loss		--	940	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	1580	2000	$\mu J$	
$Q_g$	Total Gate Charge	$V_{CE} = 300V, I_C = 40A,$ $V_{GE} = 15V$	--	175	250	nC
$Q_{ge}$	Gate-Emitter Charge		--	25	40	nC
$Q_{gc}$	Gate-Collector Charge		--	60	90	nC
$L_e$	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH



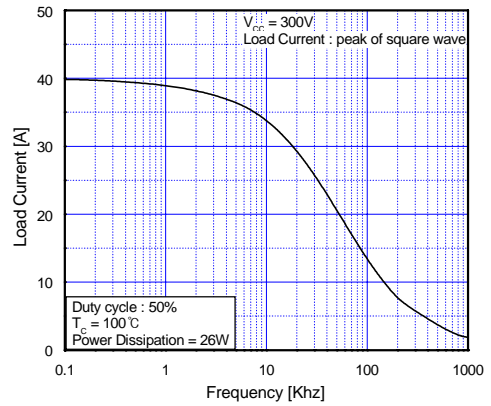
**Fig 1. Typical Output Characteristics**



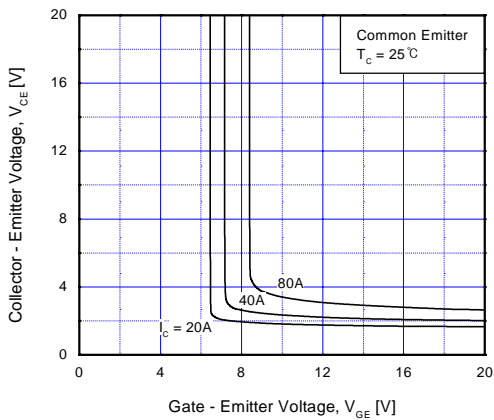
**Fig 2. Typical Saturation Voltage Characteristics**



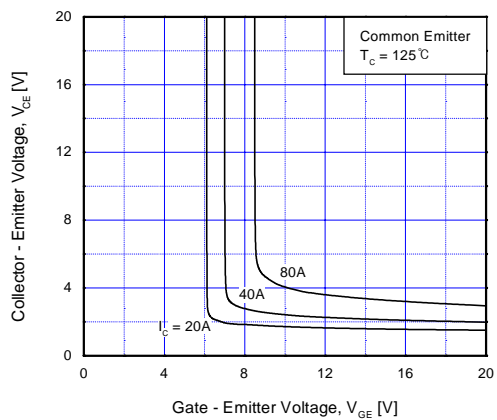
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



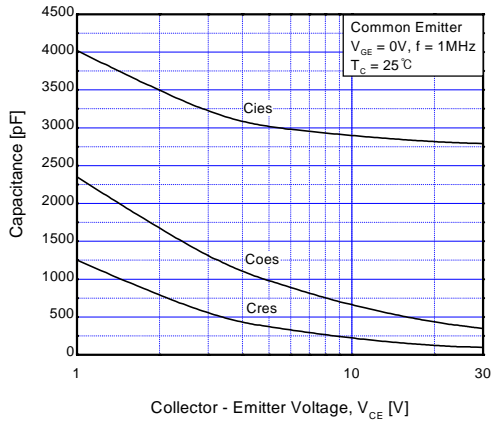
**Fig 4. Load Current vs. Frequency**



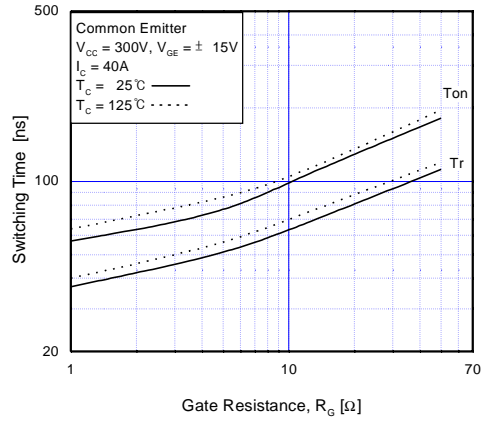
**Fig 5. Saturation Voltage vs.  $V_{GE}$**



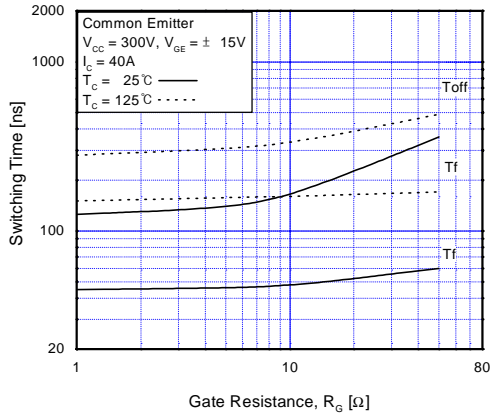
**Fig 6. Saturation Voltage vs.  $V_{GE}$**



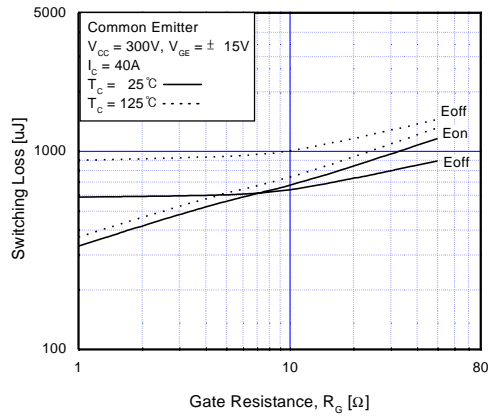
**Fig 7. Capacitance Characteristics**



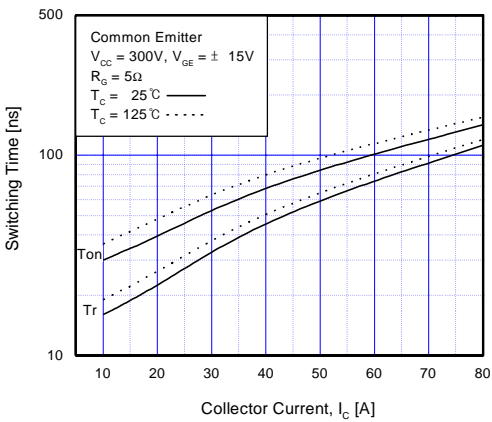
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



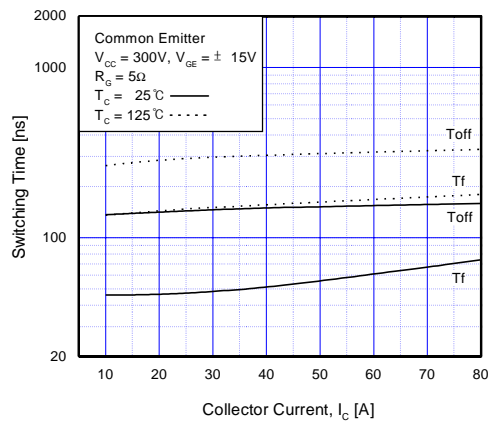
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



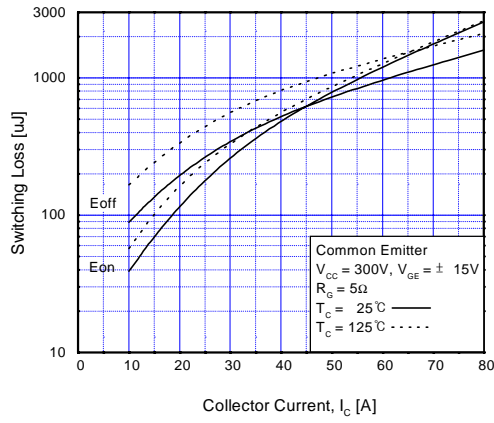
**Fig 10. Switching Loss vs. Gate Resistance**



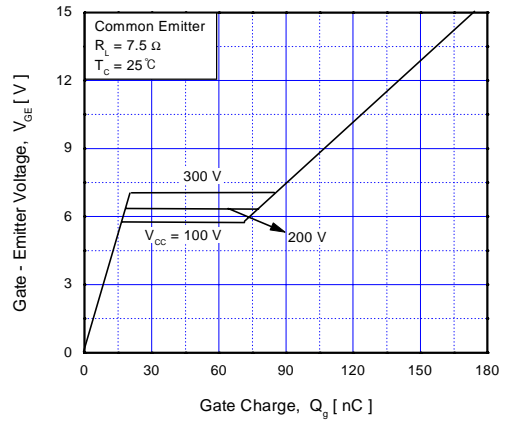
**Fig 11. Turn-On Characteristics vs. Collector Current**



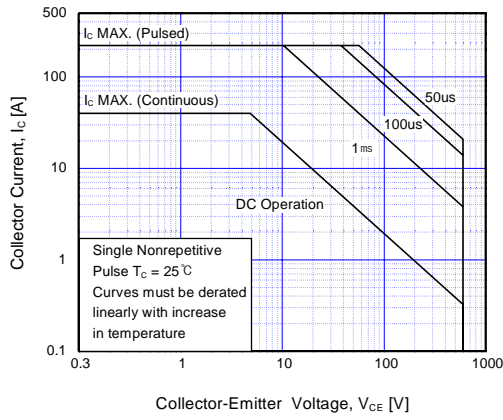
**Fig 12. Turn-Off Characteristics vs. Collector Current**



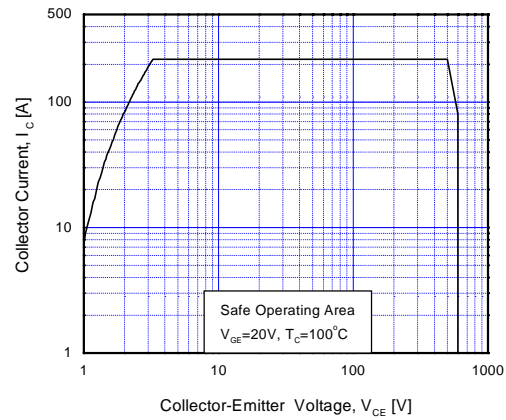
**Fig 13. Switching Loss vs. Collector Current**



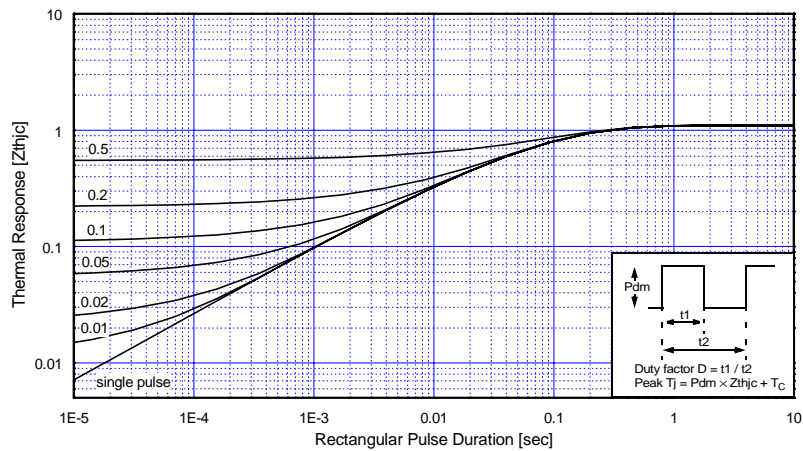
**Fig 14. Gate Charge Characteristics**



**Fig 15. SOA Characteristics**



**Fig 16. Turn-Off SOA Characteristics**

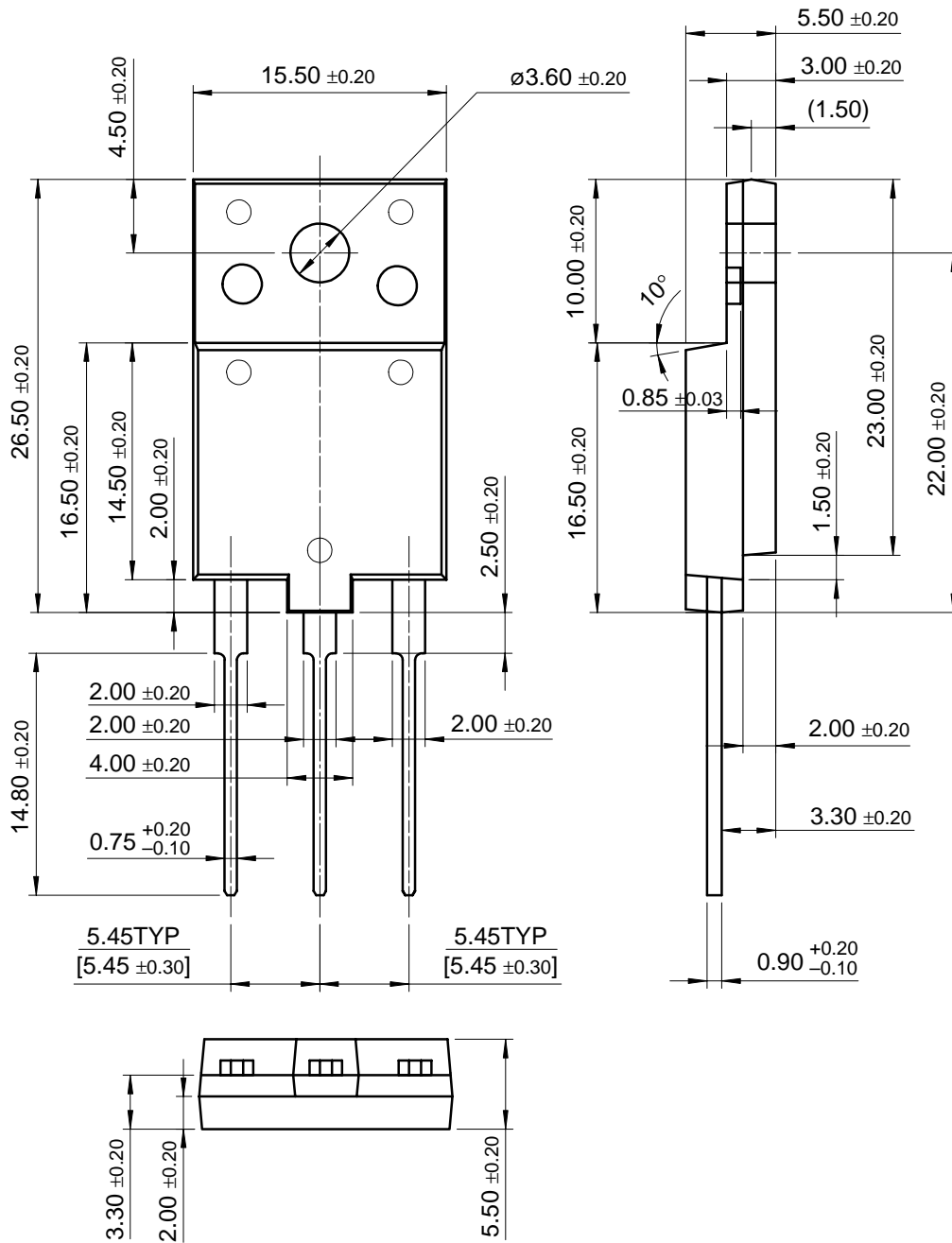


**Fig 17. Transient Thermal Impedance of IGBT**

Package Dimension

TO-3PF

SGF80N60UF



Dimensions in Millimeters

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